HD31130
SOLID STATE HIGH POWER AMPLIFIER

FEATURES

Class A GaAsFET design
Instantaneous wide Bandwidth
Built-in protection circuits
High reliability and ruggedness

ELECTRICAL SPECIFICATIONS

Parameter	Specification	Notes
Operating Frequency Range	1.0 - 8.0 GHz	
Power Output Past	6.0 Watt Min	CW
Small Signal Gain	38 dB Min	
Power Gain Flatness	4.0 dB p-p Max	
Input Return Loss	10 dB Min	
Harmonics	>20 dBc	At rated Pout
Noise Figure	8.0 dB Max	
Spurious	>60 dBc	Non Harmonics
Operating Voltage	15 VDC ±0.5 V	
Current Consumption	3.0 Amp Max	At rated Pout
Max Input Power	+8 dBm Max	Without damage
Load VSWR Protection	5 : 1	

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Case Temperature	-20 to +75 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non Condensation

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions	100 X 100 X 27mm	Excluding Connectors
Weight	TBD	
RF Connectors In/Out	SMA female	Cover Flange
DC Power / Interface Connector	9-Pin D Sub	
Cooling	External Heatsink	Forced air required

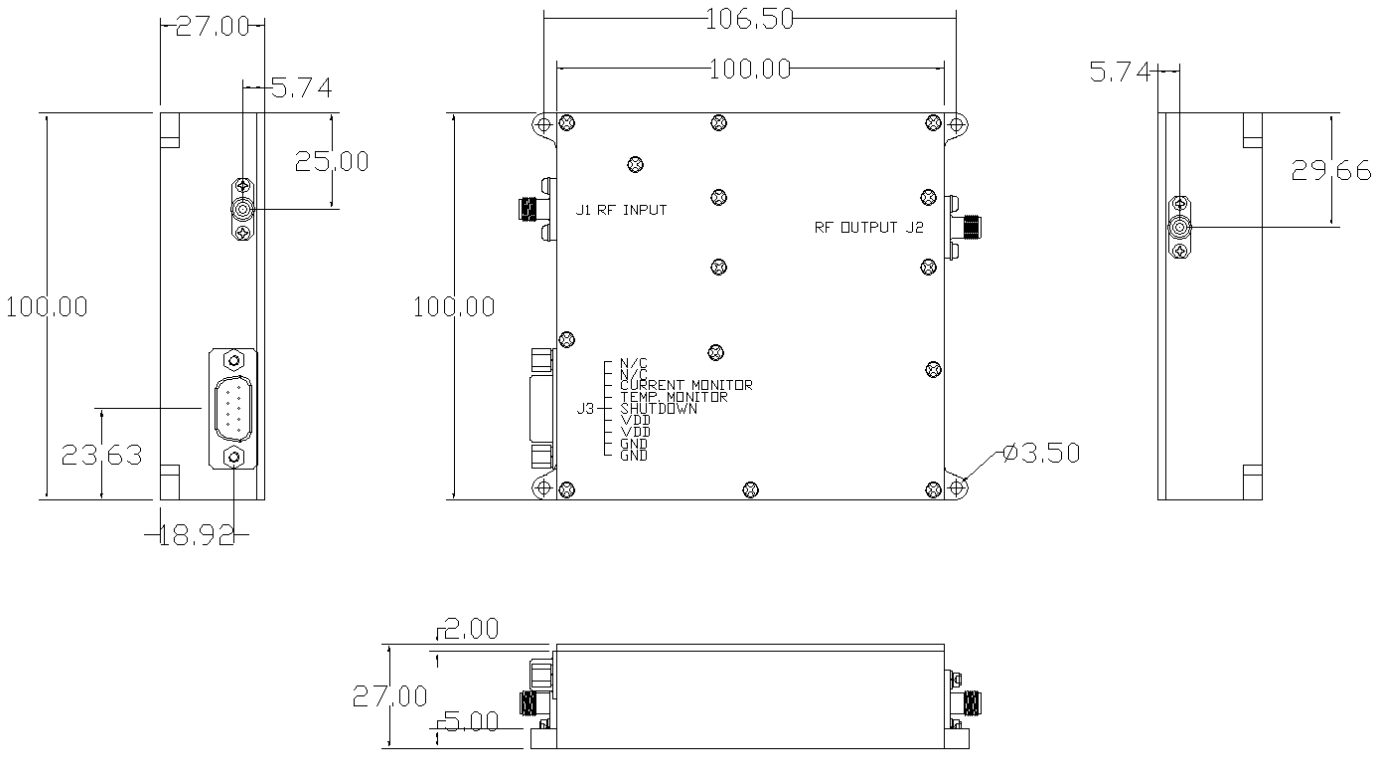
D-SUB CONNECTOR PIN ASSIGNMENT

Pin	Function	Description
1		N/A
2		N/A
3	Current Sensor	I_D@20mV/100mA Typ
4	Temp Sensor	V_T@10mV/°C + 500mV Typ
5	Shutdown	TTL
6,7	VDD	15VDC
8,9	GND	Ground

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OUTLINE DRAWING



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